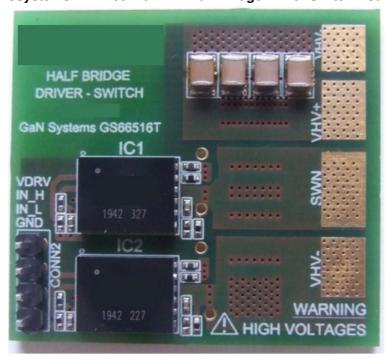


# **ALLEGRO** microsystems APEK85110-D1-E Half-Bridge Driver Switch Board User Manual

Home » ALLEGRO microsystems » ALLEGRO microsystems APEK85110-D1-E Half-Bridge Driver Switch Board User Manual ™

ALLEGRO microsystems APEK85110-D1-E Half-Bridge Driver Switch Board User Manual



#### **Contents**

- 1 Description
- 2 Quick Start Guide
- 3 Enable and Start

#### **Sequence**

- **4 Measurement Points**
- **5 Bipolar Gate Drive**
- **6 Propagation Delay**
- 7 Double Pulse Test
- **8 Test Results**
- 9 APEK85110 SCHEMATIC
- 10 PCB Layout
- 11 Revision History
- 12 Documents / Resources
  - 12.1 References
- 13 Related Posts

## **Description**

The Allegro APEK85110-D1-E Half-Bridge Driver Switch Board is a demo board containing two AHV85110 GaN FET drivers and two GaN FETs in a half-bridge configuration.

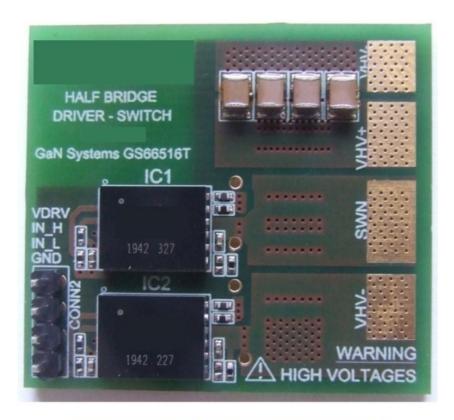


Figure 1: APEK85110 Evaluation Board

The APEK85110 can be used to perform double pulse tests (see Double Pulse Test section) or to interface the half bridge to an existing LC power section, as shown below.

The isolated AHV85110 driver does not require secondary-side power or bootstrap components. Gate drive power is supplied to the secondary side from the primary-side supply voltage, VDRV. The amplitude of the gate drive can be varied by varying VDRV between 7 and 15 V.

DO NOT TOUCH THE BOARD WHEN IT IS ENERGIZED AND ALLOW ALL COMPONENTS TO DISCHARGE COMPLETELY PRIOR HANDLING THE BOARD.

HIGH VOLTAGE CAN BE EXPOSED ON THE BOARD WHEN IT IS CONNECTED TO POWER SOURCE. EVEN BRIEF CONTACT DURING OPERATION MAY RESULT IN SEVERE INJURY OR DEATH.

Ensure that appropriate safety procedures are followed. This evaluation kit is designed for engineering evaluation in a controlled lab environment and should be handled by qualified personnel ONLY. Never leave the board operating unattended.



#### **WARNING**

Some components can be hot during and after operation. There is NO built-in electrical or thermal protection on this evaluation kit. The operating voltage, current, and component temperature should be monitored closely during operation to prevent device damage.



## **CAUTION**

This product contains parts that are susceptible to damage by electrostatic discharge (ESD). Always follow ESD prevention procedures when handling the product.

#### **Quick Start Guide**

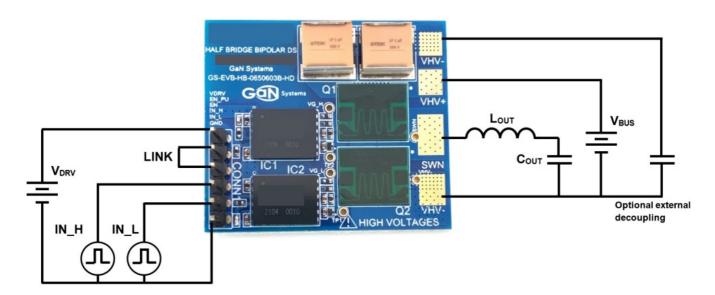


Figure 2: APEK85110 Quick Start

- 1. Apply VDRV = 12 V
- 2. Link pins EN\_PU and EN (if not using external Enable control)
- 3. Apply input gate signals, with adequate dead time, to the IN\_L and IN\_H inputs.
- 4. Convenient test points are located on the test board as shown above. A suitable differential oscilloscope should be used to monitor the high-side gate signal from VGH to VSW.

#### Gate Pull-Up and Pull-Down Resistors

The AHV85110 gate driver has independent outputs for the gate pull-up and gate pull-down allowing control of the on and off rise and fall times.

The default values for these resistors are:

• OUTPU: R1 and R5 = 10  $\Omega$ • OUTPD: R3 and R7 = 1  $\Omega$ 

These values can be modified to suit the application.

## **Enable and Start Sequence**

The AHV85110 has an open-drain enable pin (EN) to facilitate a system level wired-AND startup.

The AHV85110 has an open-drain enable pin (EN) to facilitate a system level wired-AND startup.

When the enable pin is externally pulled low, the driver is forced into a low-power mode. The driver output is pulled low in this mode.

In the event of an internal fault condition, such as UVLO, this pin is actively pulled low internally by the driver. During normal operation, the pin is released by the driver, and must be pulled high with an external pull-high resistor. This functionality can be used by the PWM controller to indicate that it can start sending IN pulses to the driver. It is typically wired-AND with the controller enable pin as shown in Figure 3.

The APEK85110 evaluation board provides direct access to the EN pin on connector CONN1. Internally the board contains a 100 k $\Omega$  pull-up resistor connected from VDRV to the EN\_PU pin on connector CONN1—see schematic in Figure 12. If external control of the enable function is not required, pins EN and EN\_PU must be linked together on CONN1 to make use of the internal 100 k $\Omega$  pull-up resistor to enable the driver. If the EN pin is left floating, the drivers will not respond to INL or INH input signals.

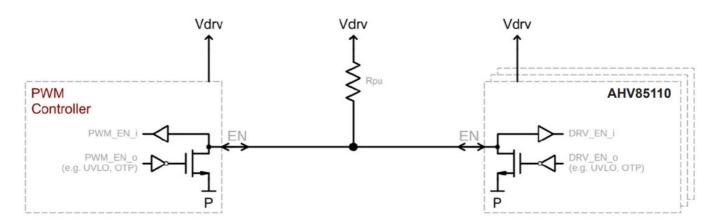


Figure 3: AHV85110 Wired-AND Enable

The start up sequence of the AHV85110 is shown in Figure 4. Time tSTART is defined as the time after which VDRV reaches the UVLO rising level to the AHV85110 releasing the EN internal pull down.

**IMPORTANT:** the IN signal must not be applied before the EN pin has been released.

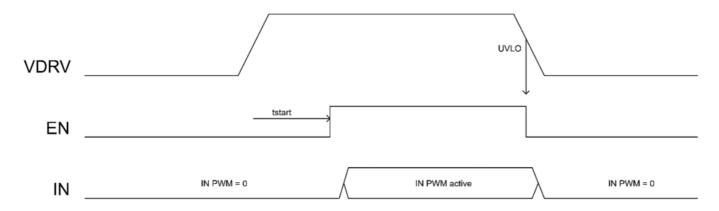


Figure 4: AHV85110 Start-Up Sequence

#### **Measurement Points**

The APEK85110 evaluation board contains convenient test points for monitoring the high- and low-side gate drives as well as the switch node as shown in Figure 5.

When measuring VGS\_H, use a differential probe with suitable ratings for the applied bus voltage. The APEK85110 evaluation board uses a bipolar gate drive arrangement as shown in Figure 6. When measuring VGS, both gate drives are measured relative to the source of their associated GaN FET. Therefore, the off-state voltage will be negative.

It is important to use a low-inductance scope probe ground lead as shown to avoid pickup of spurious switching noise.

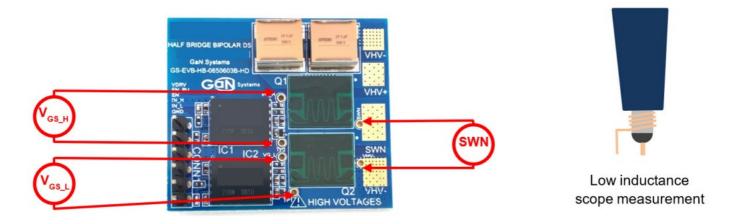


Figure 5: Measurements Points

#### **Bipolar Gate Drive**

Due to the high rate of change of voltages and currents in power switching circuits, unwanted inductor currents and capacitor voltage drops can be created.

One such example is the false turn on of a FET due to a dv/dt event. In a half-bridge circuit, after the low-side FET has been turned off and a suitable dead-time has elapsed, the high-side FET is turned on. This produces a rapidly changing switch node voltage at the drain of the low-side FET. This voltage will produce a capacitor current,

$$iCGD = CGD \times (dVDS L / dt)$$

flowing in the gate-drain capacitance, CGD, and driver output. It will cause the voltage on the gate of the low-side FET to rise. If this voltage spike peaks beyond the threshold voltage, VTH, the FET will conduct. Considering that

the high-side FET is also conducting, this can result in a potentially destructive shoot-through event.

The APEK85110 evaluation board uses a bipolar gate drive arrangement which is useful to mitigate against the effects of gate-drain capacitor currents. The secondary supply voltage, VSEC, is a function of the primary supply voltage, VDRV. The zener diode, CR1, will regulate the positive turn-on voltage of the GaN FET. During the turn-off of period, the gate voltage will be negative with a value of:

VGS OFF = VSEC - VZENER. VSEC is typically 9 V

This negative VGS\_OFF voltage allows more margin before the threshold voltage can be reached.

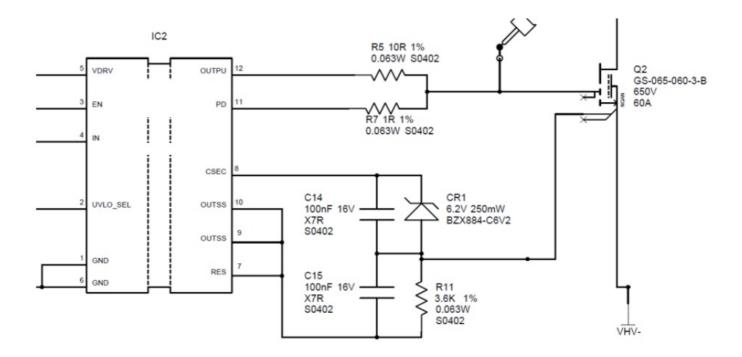


Figure 6: Bipolar Gate Drive Schematic

# **Propagation Delay**

- VDRV = 12 V
- Input = 100 kHz
- RPU =  $10 \Omega$ , RPD =  $1 \Omega$
- Power train unloaded, i.e., VHV+ = 0 V.

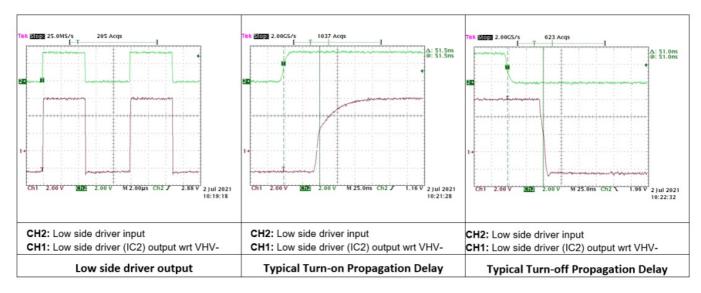


Figure 7: Typical Driver Output at 100 kHz

## **Double Pulse Test**

## **Theory**

The double pulse test is used to evaluate the switching characteristics of a power switch under hard switching but in a safe manner.

For a low-side switch, the set up is as shown below:

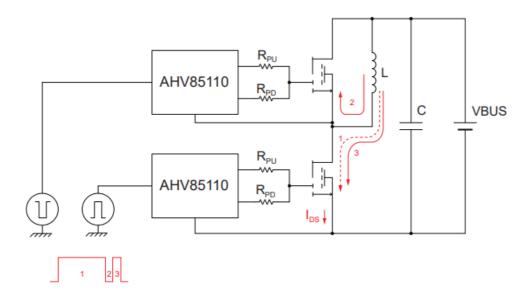


Figure 8: Double Pulse Test

The low-side switch is driven with two pulses as shown below. The high-side switch can be held off or driven with the inverse of the low-side gate switch (with adequate dead time).

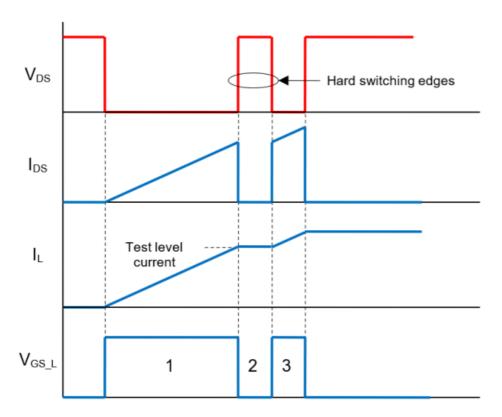


Figure 9: Double Pulse Test Waveforms

An inductor is placed in parallel with the high-side switch. The goal of this inductor is to establish the test level current in the low-side switch at the end of the first on pulse (1). The magnitude of the test level current at the end of period 1 is given by

$$IL = (VBUS \times tON_1) / L$$

During period 2, the inductor current will naturally decay. The duration of period 2 should not be too long that inductor current deviates significantly from the desired test level.

During period 3, the inductor current will again rise. Period 3 should not be so long that the inductor current rises to an excessive level.

The falling edge of pulse 1 is used to examine the hard turn-off characteristics of the switch. The rising edge of pulse 3 is used to examine the hard turn-on characteristics of the switch. By only applying these two pulses, the switches are only on for a very short time and should not overheat.

#### **Test Results**

Components	onents		
Drivers:	Allegro AHV85110		
Inductor:	49 μH, 360 mΩ Air Core		
RPU:	10 Ω		
RPD:	1 Ω		

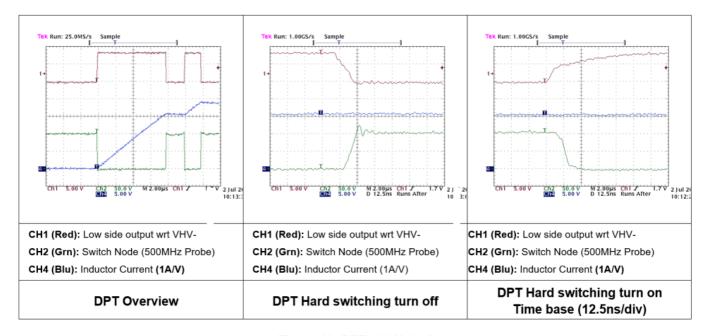


Figure 10: DPT 100 V, 15 A

#### DPT Result 400V - 62A

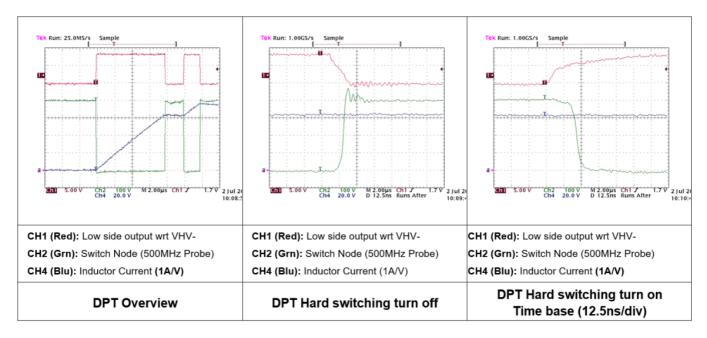


Figure 11: DPT 400 V, 62 A

# **APEK85110 SCHEMATIC**

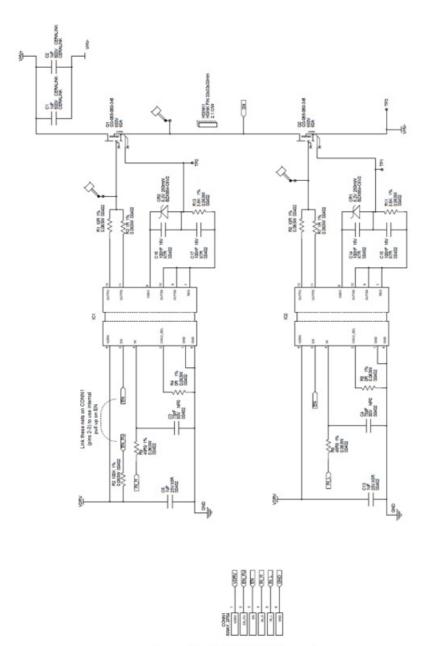


Figure 12: APEK85110 Schematic

**PCB Layout** 

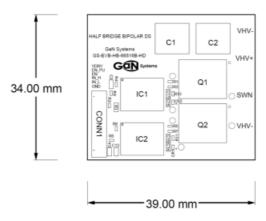


Figure 13: APEK85110 Silkscreen and Component Placement

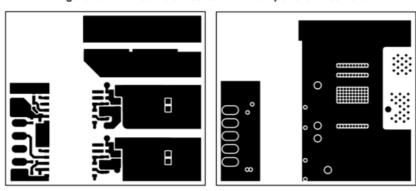


Figure 14: APEK85110 Top-Side Copper (L) and Layer 2 Copper (R)

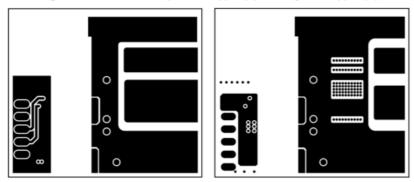


Figure 15: APEK85110 Layer 2 Copper(L) and Bottom-Side Copper (R)

APEK85110 Half-Bridge Driver Switch Board Bill Of Materials

**Table 1: Bill of Materials** 

Ite m	Ref Name	Description	Value	Qty	Manufacturer	Manufacturer PN
1	C1, C2	CAP CERALINK, 1 μF, 500 V PLZT	1 μF	2	TDK	B58031U5105M062
2	C14, C15, C1 6, C17	CAP, CER,100 nF,16 V, X7R, S0402	100 nF	4	KEMET	C0402C104K4RAL TU
3	C3, C4	CAP, CER, 75 pF, 50 V, NP0, S0402	75 pF	2	KEMET	C0402C750J5GAC TU
4	C6, C13	CAP, CER,1 μF, 25V, X5R, S 0402	1 μF	2	MURATA	GRM155R61E105K A12D
3	CONN1	HEADER, 6 WAY, 2.54 mm	6WAY, 2P54	1	WURTH	61300611121
6	CR1, CR2	DIO ZEN, 6V2, 250 mW, 2%, SOD882	BZX884-C6 V2	2	NEXPERIA	BZX884-B6V2,315
7	IC1, IC2	GaN FET Driver	AHV85110	2	HEYDAY IC	HEY1011-L12
8	Q1, Q2	NGAN GS-065-060-3-B 650 V 60A	GS-065-060 -3-B	2	GAN SYSTE MS	GS-065-060-3-B
9	R1, R5	RES, SMD, 10R, 0.063W, 1 %, S0402	10 Ω	2	VISHAY	CRCW040210R0FK ED
10	R11, R13	RES, SMD, 3K6, 0.063W, 1 %, S0402	3.6 kΩ	2	PANASONIC	ERJ2RKF3601X
11	R2	RES, SMD, 100K, 0.063W, 1 %, S0402	100 kΩ	1	PANASONIC	ERJ2GEJ104X
12	R3, R7	RES, SMD, 1R0, 0.063W, 1 %, S0402	1 Ω	2	VISHAY	CRCW04021R00FK ED
13	R4, R8	RES, SMD, 0R0, 0.063W, 1 %, S0402	0 Ω	2	VISHAY	RCG04020000Z0E D
14	R6, R9	RES, SMD, 49R9, 0.063W, 1 %, S0402	49.9 Ω	2	VISHAY	CRCW040249R9FK ED

# **Revision History**

Number	Date	Description
_	August 30, 2022	Initial release

## Copyright 2022, Allegro MicroSystems.

Allegro MicroSystems reserves the right to make, from time to time, such departures from the detail specifications as may be required to permit improvements in the performance, reliability, or manufacturability of its products. Before placing an order, the user is cautioned to verify that the information being relied upon is current.

Allegro's products are not to be used in any devices or systems, including but not limited to life support devices or systems, in which a failure of

Allegro's product can reasonably be expected to cause bodily harm.

The information included herein is believed to be accurate and reliable. However, Allegro MicroSystems assumes no responsibility for its use; nor for any infringement of patents or other rights of third parties which may result from its use.

Copies of this document are considered uncontrolled documents.

For the latest version of this document, visit our website: <a href="https://www.allegromicro.com">www.allegromicro.com</a>

## **Advance Information**

Subject to Change Without Notice August 30, 2022

Allegro MicroSystems 955 Perimeter Road Manchester, NH 03103-3353 U.S.A. www.allegromicro.com

#### **Documents / Resources**



ALLEGRO microsystems APEK85110-D1-E Half-Bridge Driver Switch Board [pdf] User Manual

APEK85110-D1-E Half-Bridge Driver Switch Board, APEK85110-D1-E, Half-Bridge Driver Switch Board, Bridge Driver Switch Board, Switch Board, Board

# References

Allegro MicroSystems | Innovation with Purpose

Manuals+,